

T-4-05

TYPE
NAME

ML3101, ML3401, ML3411

DESCRIPTION

Mitsubishi ML3XX1 are AlGaAs laser diodes emitting light beams around 815nm wavelength. They lase by applying forward current exceeding threshold values, and emit light power of about 3mW/facet at an operating current of around 10mA in excess of the threshold current. They operate, under CW or pulse conditions according to input current, at case temperatures up to 60°C.

ML3XX1 are hermetically sealed devices having a Si photodiode for monitoring the light output. Output current of the photodiode can be used for automatic control of the operating currents or case temperatures of the lasers. They are well suited for light sources in optical communication systems.

FEATURES

- Stable fundamental transverse mode oscillation
- Small astigmatism
- Low threshold current, low operating current
- Si photodiode is installed in the laser package
- High reliability, long operation life

APPLICATION

Digital communication systems, laser beam printers, optical products code readers, optical distance meter

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
P _O	Light output	CW	3.5	mW
		Pulse (Note 1)	6	
V _{RL}	Reverse voltage (Laser diode)	—	3	V
V _{RD}	Reverse voltage (Photodiode)	—	15	V
I _{FD}	Forward current (Photodiode)	—	10	mA
T _C	Case temperature	—	-40~+60	°C
T _{stg}	Storage temperature	—	-55~+100	°C

Note 1 : Duty less than 50%, pulse width less than 1μs.

ELECTRICAL/OPTICAL CHARACTERISTICS (T_C=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{th}	Threshold current	CW	—	20	40	mA
I _{OP}	Operating current	CW, P _O =3mW	—	30	50	mA
V _{OP}	Operating voltage (Laser diode)	CW, P _O =3mW	—	1.8	2.5	V
P _O	Light output	CW, I _F =I _{th} +10mA	—	3	—	mW
λ _P	Lasing wavelength	CW, P _O =3mW	795	815	905	nm
θ	Full angle at half maximum	CW, P _O =3mW	8	11	18	deg.
θ _⊥			20	30	50	
I _m	Monitoring output current	CW, P _O =3mW V _{RD} =1V R _L =10Ω (Note 2)	0.1	0.3	0.7	mA
I _D	Dark current (Photodiode)	V _{RD} =10V	—	—	0.5	μA
C _t	Capacitance (Photodiode)	V _R =0V, f=1MHz	—	7	—	pF

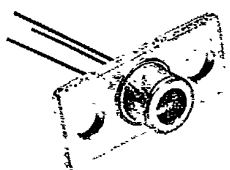
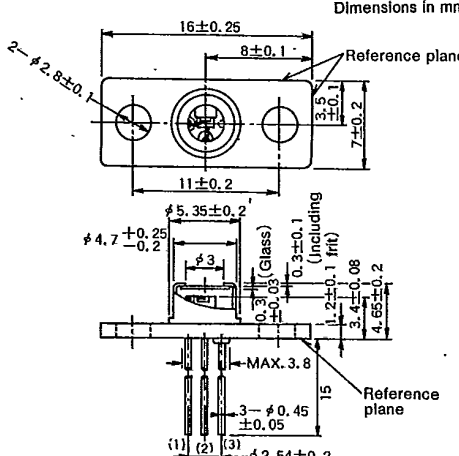
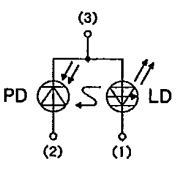
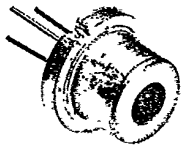
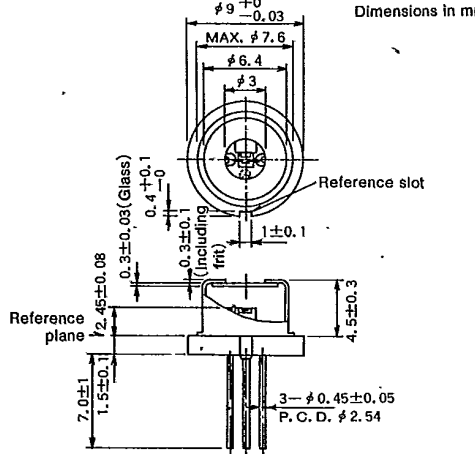
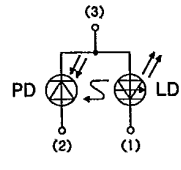
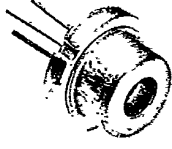
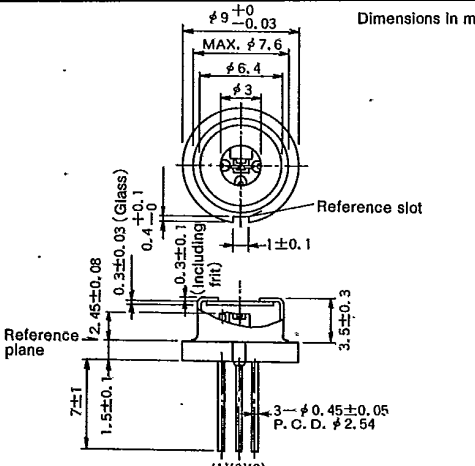
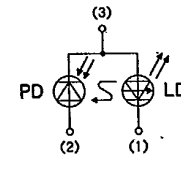
Note 2 : R_L is load resistance of the photodiode.

MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 3LE D ■ 6249829 0014036 6 ■ MITS
FOR OPTICAL INFORMATION SYSTEMS

T-41-05

OUTLINE DRAWINGS

<p>ML3101</p> 	<p>Dimensions in mm</p> 	
<p>ML3401</p> 	<p>Dimensions in mm</p> 	
<p>ML3411</p> 	<p>Dimensions in mm</p> 	

MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 3LE D 6249829 0014037 & MITS

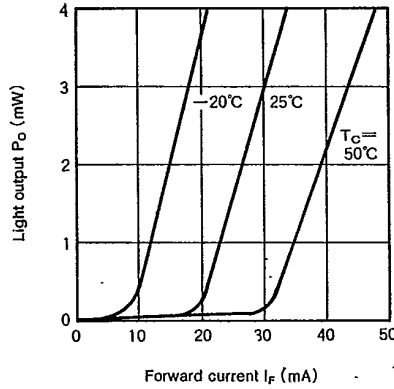
FOR OPTICAL INFORMATION SYSTEMS

T-41-05

1 Light output vs. forward current

Typical light output vs. forward current characteristics are shown in Fig. 1. The threshold current for lasing is typically 20mA at room temperature. Above the threshold, the light output increases linearly with current, and no kinks are observed in the curves. As can be seen in Fig. 1, the threshold current and slope efficiency (dP_o/dI_f) depends on case temperature of the lasers. This suggests that automatic control of temperature or current is necessary to keep the light output constant since temperature variation is inevitable in practical systems. The automatic controls should be such that the maximum ratings for the light output and the case temperature are not exceeded. "OPERATING CONSIDERATIONS" gives an example of an automatic light output control circuit.

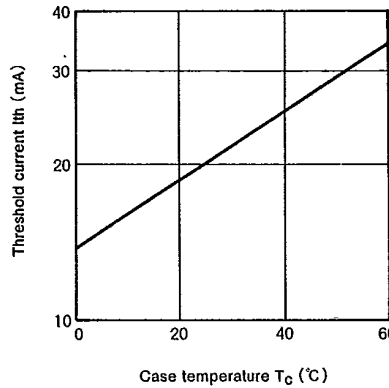
Fig. 1 Light output vs. forward current



2 Temperature dependence of threshold current (I_{th})

A typical temperature dependence of the threshold current is shown in Fig. 2. The characteristic temperature T_0 of the threshold current is typically 65K in $T_c \leq 50^\circ\text{C}$, where the definition of T_0 is $I_{th} \propto \exp(T_c/T_0)$

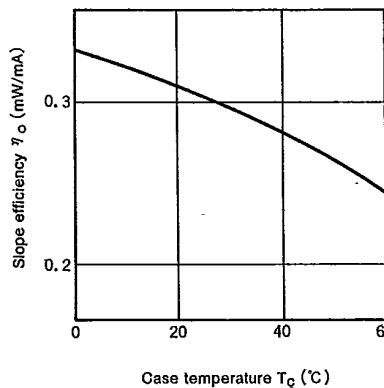
Fig. 2 Temperature dependence of threshold current



3 Temperature dependence of slope efficiency

A typical temperature dependence of the slope efficiency η_o is shown in Fig. 3. The gradient is $-0.0015\text{mW}/\text{mA}/^\circ\text{C}$.

Fig. 3 Temperature dependence of slope efficiency



MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 3LE D ■ 6249829 0014038 T ■ MIT5

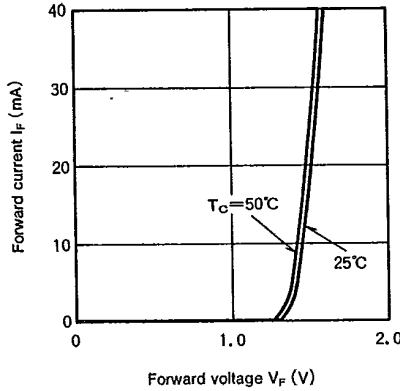
FOR OPTICAL INFORMATION SYSTEMS

T-41-05

4 Forward current vs. voltage

Typical forward current vs. voltage characteristics are shown in Fig. 4. In general, as the case temperature rises, the forward voltage V_F decreases slightly against the constant current I_F . V_F varies typically at a rate of $-2.0\text{mV}/^\circ\text{C}$ at $I_F = 1\text{mA}$.

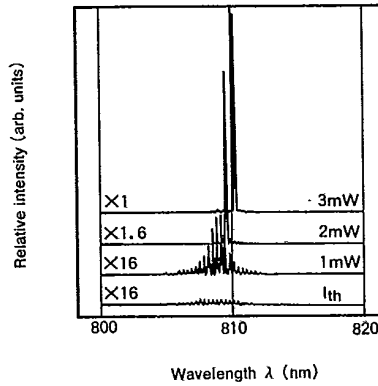
Fig. 4 Forward current vs. voltage characteristics



5 Emission spectra

Typical emission spectra under CW operation are shown in Fig. 5. In general, at an output of 3mW, single mode is observed. The peak wavelength depends on the operating case temperature and forward current (output level).

Fig. 5 Emission spectra under CW operation



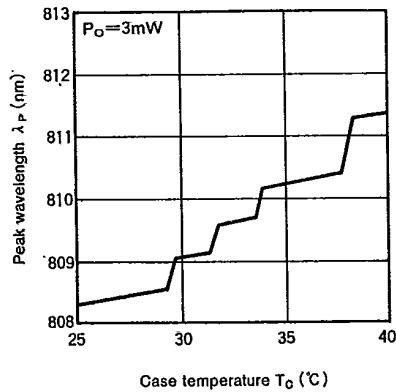
6 Temperature dependence of peak wavelength

A typical temperature dependence of the peak wavelength at an output of 3mW is shown in Fig. 6.

The peak wavelength of the beam shifts and jumps to adjacent longitudinal mode by variation of operating temperature.

Averaged temperature coefficient which includes the shifts and jumps is about $0.25\text{nm}/^\circ\text{C}$.

Fig. 6 Temperature dependence of peak wavelength



MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 31E D ■ 6249829 0014039 1 ■ MIT5
FOR OPTICAL INFORMATION SYSTEMS

T-41-05

7 Far-field radiation pattern

The ML3XX1 laser diodes lase in fundamental transverse (TE_{00}) mode and the mode does not change with the current. They have a typical emitting area (size of near-field pattern) of $2.2 \times 0.8 \mu m^2$. Fig. 7 and Fig. 8 show typical far-field radiation patterns in "parallel" and "perpendicular" planes.

The full angles at half maximum points (FAHM) are typically 11° and 30° .

Fig. 7 Far-field patterns in plane parallel to heterojunctions

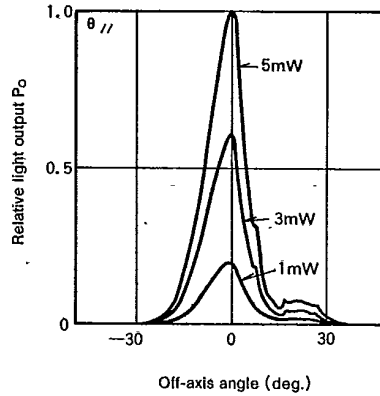
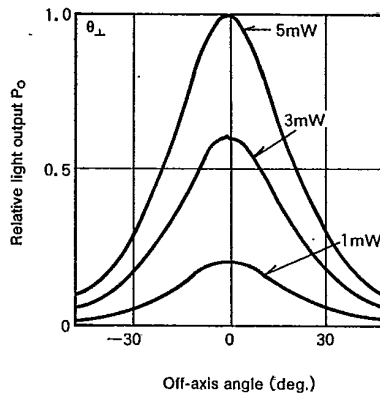


Fig. 8 Far-field patterns in plane perpendicular to heterojunctions



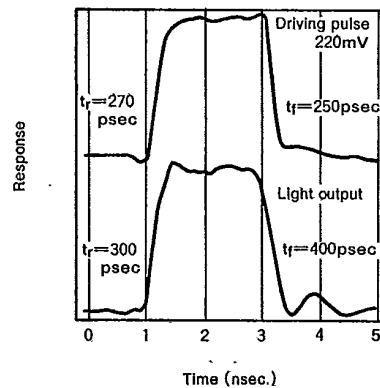
8 Pulse response waveform

In the digital optical transmission systems, the response waveform and speed of the light output against the input current pulse waveform (shown in Fig. 9 upper) is one of the main concerns.

The speed depends on the oscillation delay time, rise and fall times. In order to shorten the oscillation delay time, the laser diode is usually biased close to the threshold current since the delay time is a time for charging the junction up to the threshold. Fig. 9 shows the typical response waveform when rectangular pulse current is applied.

The output power is 3mW and bias current $I_b = I_{th}$. The rise time and the fall time in Fig. 9 are typically 0.3ns and 0.4ns. They are limited by response speed of the detector.

Fig. 9 Pulse response waveform



MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 3LE D 6249829 0014040 8 MITS

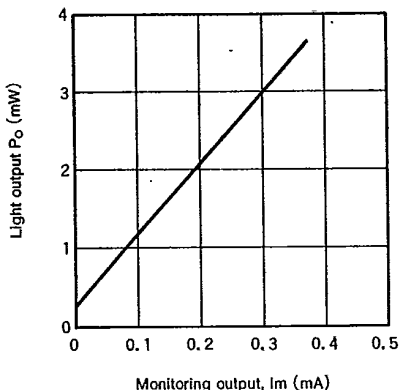
FOR OPTICAL INFORMATION SYSTEMS

T-41-05

9 Monitoring output

The laser diodes emit beams from both of their mirror surfaces, front and rear surfaces (see the outline drawing). The rear beam can be used for monitoring power of front beam since the rear beam is proportional to the front one. In the case of ML3XX1 lasers, the rear beam powers are changed into photocurrent by the monitoring photodiodes. Fig. 10 shows an example of light output vs monitoring photocurrent characteristics. Above the threshold, the monitored photocurrent linearly increases with the light output.

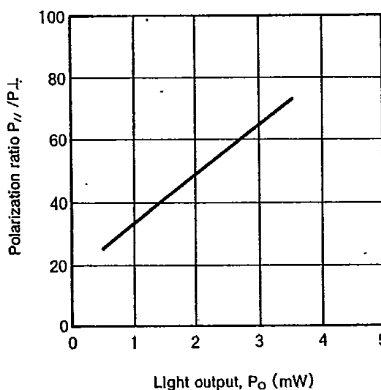
Fig. 10 Light output vs. monitoring output current



10 Polarization ratio

The polarization ratio ($P_{//}/P_{\perp}$), which is the ratio of the parallel polarized light output and the perpendicular polarized one, vs. total light output characteristics is shown in Fig. 11. The polarization ratio increases with the light power.

Fig. 11 Polarization ratio vs. light output

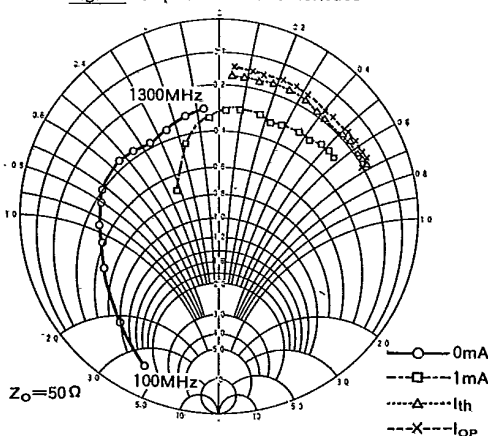


11 Impedance characteristics

Typical impedance characteristics of the ML3XX1, with lead lengths of 2mm, is shown in Fig. 12 with the bias currents as the parameter. Test frequency is swept from 100MHz to 1300MHz with 100MHz steps.

Above the threshold current, the impedance of the ML3XX1 is nearly equal to a series connection of a resistance of 5 ohm and an inductance of 5nH.

Fig. 12 Impedance characteristics



MITSUBISHI LASER DIODES
ML3XX1 SERIES

MITSUBISHI (DISCRETE SC) 3LE D 6249829 0014041 T MIT5

FOR OPTICAL INFORMATION SYSTEMS

T-41-05

12 Astigmatic focal distance

There seems to be a difference in luminous point in the parallel and perpendicular direction with the laser beam. This distance between the two points is the astigmatic focal distance. Therefore, when the laser beam is focused, there is a difference in focal point in the two directions.

The typical astigmatic focal distance at NA=0.7 of ML3XX1 is shown in Fig. 13.

Fig. 13 Astigmatic focal distance

